

N-Channel 80 V (D-S) Super Trench Power MOSFET

PRODUCT SUMMARY	
V_{DS} (V)	80
$R_{DS(on)}$ (Ω) at $V_{GS} = 10$ V	0.006
$R_{DS(on)}$ (Ω) at $V_{GS} = 6$ V	0.0075
I_D (A)	16
Configuration	Single

FEATURES

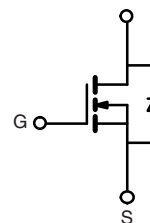
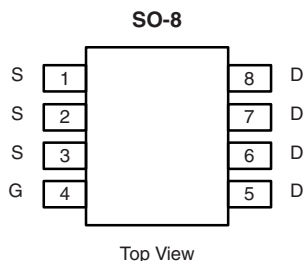
- Super Trench technology Power MOSFET
- Excellent gate charge x R_{ds} (on) product(FOM)
- Very low on-resistance R_{ds} (on)
- 100 % R_g and UIS Tested



RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- DC/DC Converter
- Ideal for hgh-frequency switching and synchronous



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)				
PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-Source Voltage	V_{DS}	80	V	
Gate-Source Voltage	V_{GS}	± 20		
Continuous Drain Current	I_D	$T_C = 25$ °C	16	
		$T_C = 125$ °C	9	
Continuous Source Current (Diode Conduction)	I_S	6	A	
Pulsed Drain Current ^a	I_{DM}	67		
Single Pulse Avalanche Current	I_{AS}	50		
Single Pulse Avalanche Energy	E_{AS}	L = 0.1 mH	125	mJ
Maximum Power Dissipation ^a			P_D	
		$T_C = 125$ °C		2.3
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to + 175	°C	

THERMAL RESISTANCE RATINGS			
PARAMETER	SYMBOL	LIMIT	UNIT
Junction-to-Ambient	R_{thJA}	80	°C/W
Junction-to-Foot (Drain)			

Notes

- Pulse test; pulse width ≤ 300 μ s, duty cycle ≤ 2 %.
- When mounted on 1" square PCB (FR-4 material).
- Parametric verification ongoing.

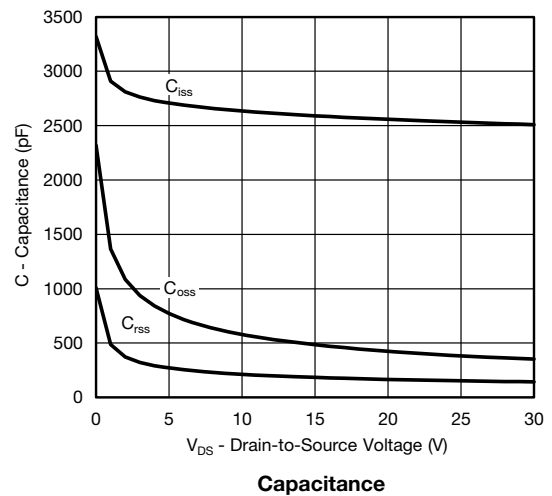
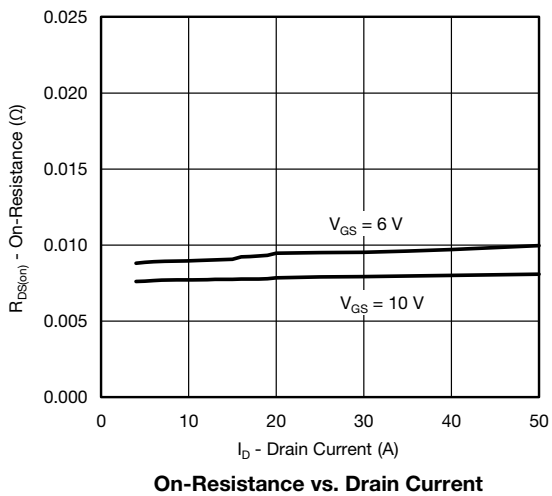
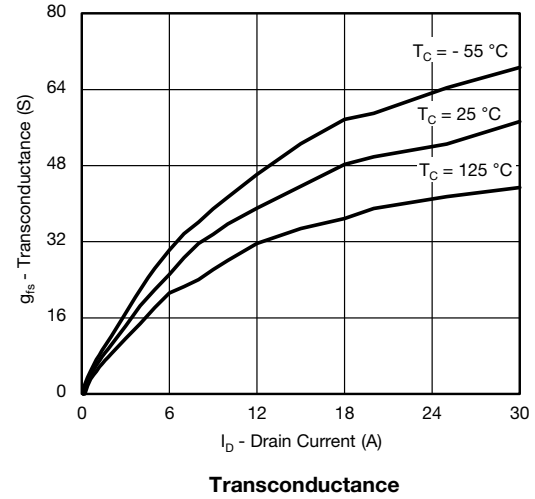
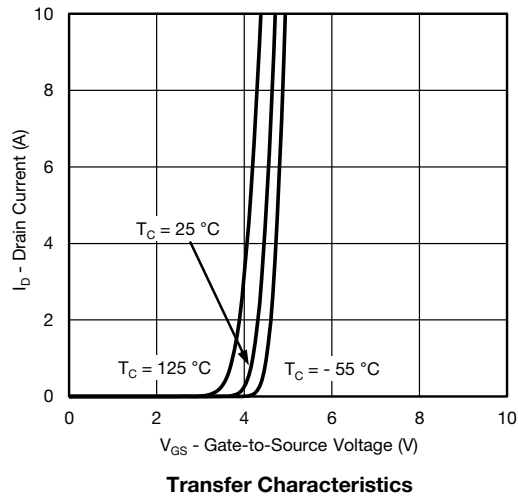
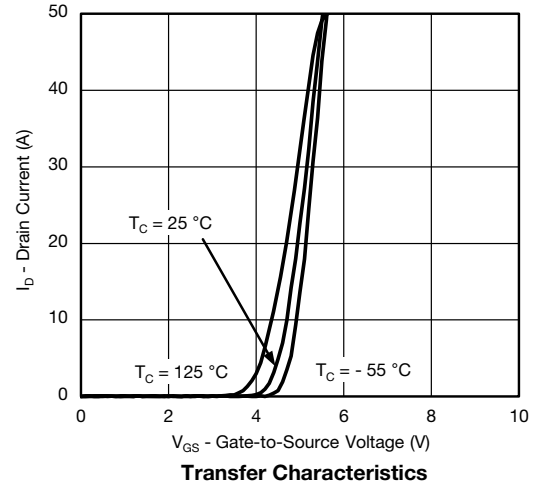
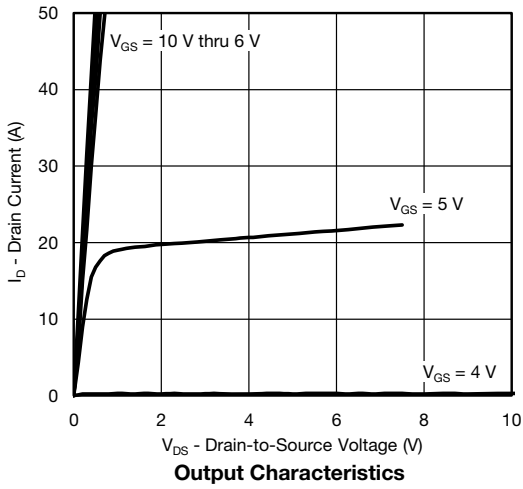
SPECIFICATIONS ($T_C = 25\text{ }^\circ\text{C}$, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0, I_D = 250\text{ }\mu\text{A}$		80	-	-	V
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$		2.5	3.0	3.5	
Gate-Source Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$		-	-	± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS} = 0\text{ V}$	$V_{DS} = 60\text{ V}$	-	-	1.0	μA
		$V_{GS} = 0\text{ V}$	$V_{DS} = 80\text{ V}, T_J = 125\text{ }^\circ\text{C}$	-	-	50	
		$V_{GS} = 0\text{ V}$	$V_{DS} = 80\text{ V}, T_J = 175\text{ }^\circ\text{C}$	-	-	250	
On-State Drain Current ^a	$I_{D(on)}$	$V_{GS} = 10\text{ V}$	$V_{DS} \geq 5\text{ V}$	30	-	-	A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$	$I_D = 6\text{ A}$	-	0.006	-	Ω
		$V_{GS} = 10\text{ V}$	$I_D = 6\text{ A}, T_J = 125\text{ }^\circ\text{C}$	-	0.011	-	
		$V_{GS} = 10\text{ V}$	$I_D = 6\text{ A}, T_J = 175\text{ }^\circ\text{C}$	-	0.015	-	
		$V_{GS} = 6\text{ V}$	$I_D = 5\text{ A}$	-	0.0075	-	
Forward Transconductance ^b	g_{fs}	$V_{DS} = 15\text{ V}, I_D = 6\text{ A}$		-	25	-	S
Dynamic^b							
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}$	$V_{DS} = 25\text{ V}, f = 1\text{ MHz}$	-	2531	3165	μF
Output Capacitance	C_{oss}			-	382	480	
Reverse Transfer Capacitance	C_{rss}			-	153	195	
Total Gate Charge ^c	Q_g	$V_{GS} = 10\text{ V}$	$V_{DS} = 30\text{ V}, I_D = 12\text{ A}$	-	45	68	nC
Gate-Source Charge ^c	Q_{gs}			-	9.9	-	
Gate-Drain Charge ^c	Q_{gd}			-	11.2	-	
Gate Resistance	R_g	$f = 1\text{ MHz}$		0.40	0.87	1.30	Ω
Turn-On Delay Time ^c	$t_{d(on)}$	$V_{DD} = 30\text{ V}, R_L = 2.5\text{ }\Omega$ $I_D \cong 12\text{ A}, V_{GEN} = 10\text{ V}, R_g = 1\text{ }\Omega$		-	13	20	ns
Rise Time ^c	t_r			-	12	18	
Turn-Off Delay Time ^c	$t_{d(off)}$			-	25	38	
Fall Time ^c	t_f			-	9	14	
Source-Drain Diode Ratings and Characteristics^b							
Pulsed Current ^a	I_{SM}			-	-	67	A
Forward Voltage	V_{SD}	$I_F = 1.7\text{ A}, V_{GS} = 0$		-	0.72	1.2	V

Notes

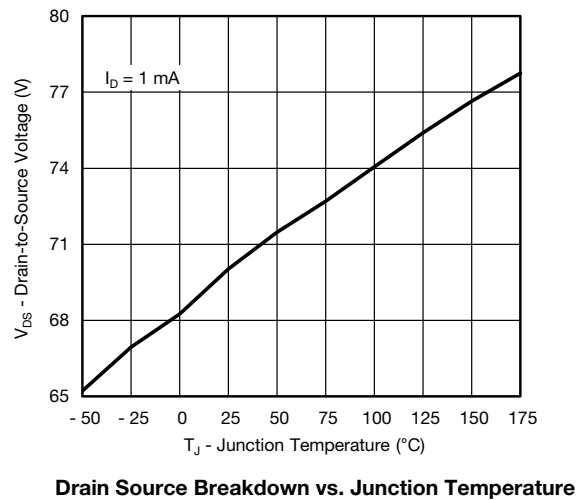
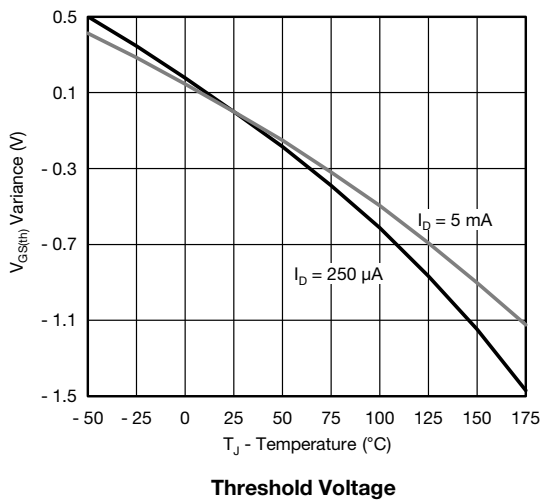
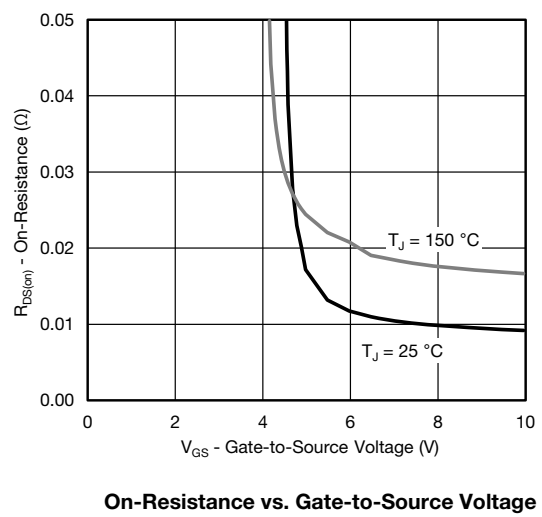
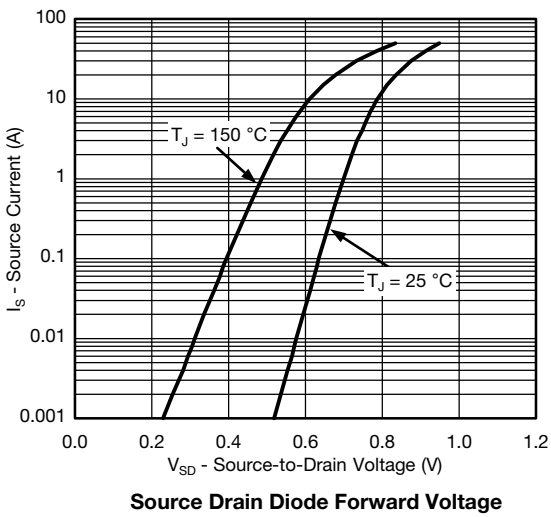
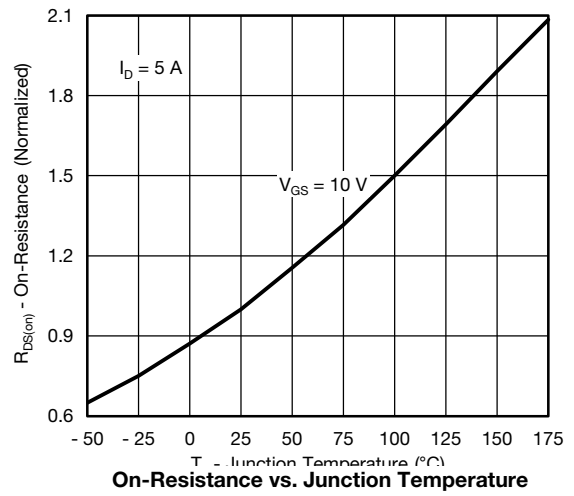
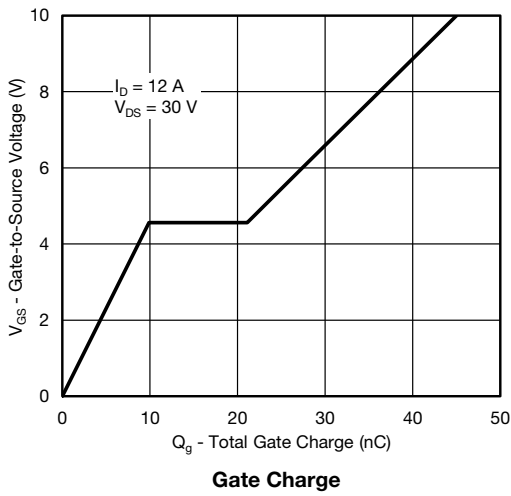
- Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
- Guaranteed by design, not subject to production testing.
- Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

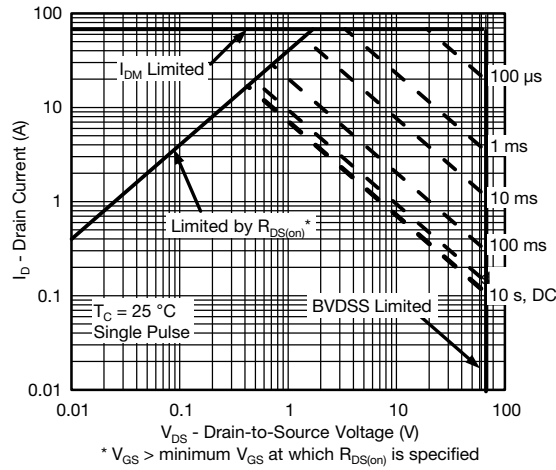
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



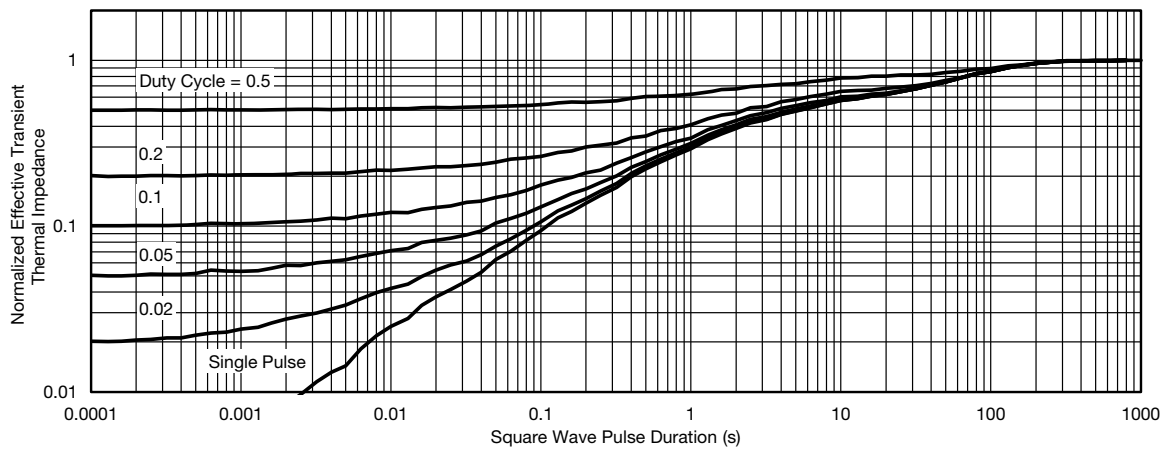
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



THERMAL RATINGS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)

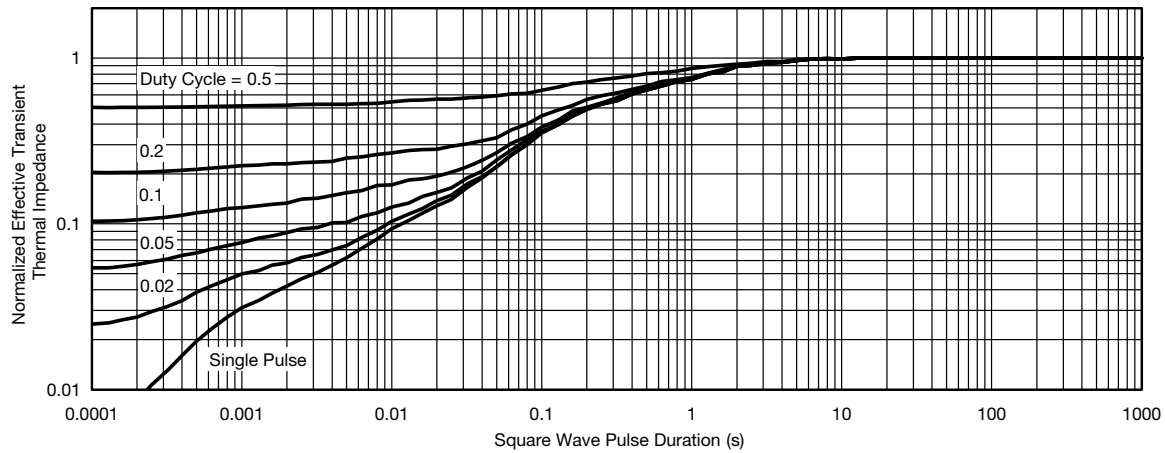


Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient

THERMAL RATINGS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Foot

Note

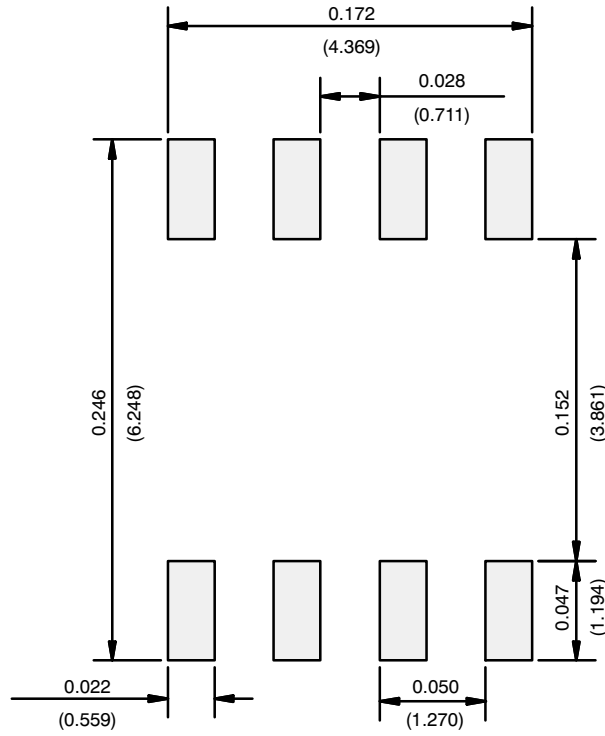
- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient ($25\text{ }^\circ\text{C}$)
 - Normalized Transient Thermal Impedance Junction-to-Foot ($25\text{ }^\circ\text{C}$)
 are given for general guidelines only to enable the user to get a “ball park” indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

SOIC (NARROW): 8-LEAD
JEDEC Part Number: MS-012



DIM	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	1.35	1.75	0.053	0.069
A ₁	0.10	0.20	0.004	0.008
B	0.35	0.51	0.014	0.020
C	0.19	0.25	0.0075	0.010
D	4.80	5.00	0.189	0.196
E	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
H	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.020
L	0.50	0.93	0.020	0.037
q	0°	8°	0°	8°
S	0.44	0.64	0.018	0.026
ECN: C-06527-Rev. I, 11-Sep-06 DWG: 5498				

RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads
Dimensions in Inches/(mm)

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